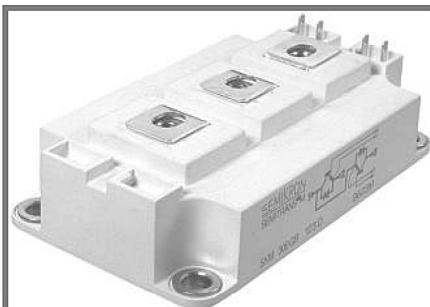


SKM 300GB125D



SEMITRANS® 3

Ultra Fast IGBT Module

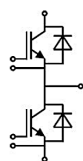
SKM 300GB125D

Features

- NPT - Non punch-through IGBT
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- High short circuit capability, self limiting
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology
- Large clearance (10 mm) and creepage distances (20 mm)

Typical Applications*

- Switched mode power supplies at $f_{sw} > 20$ kHz
- Resonant inverters up to 100 kHz
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- UPS Uninterruptable power supplies at $f_{sw} > 20$ kHz
- Electronic welders at $f_{sw} > 20$ kHz

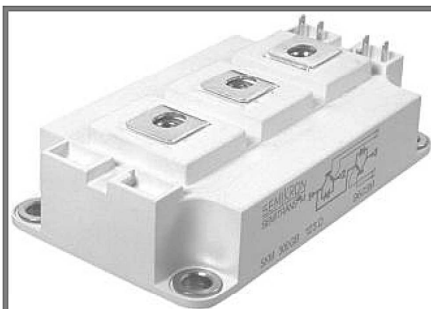


GB

Absolute Maximum Ratings			$T_c = 25\text{ }^{\circ}\text{C}$, unless otherwise specified	
Symbol	Conditions		Values	Units
IGBT				
V_{CES}	$T_j = 25\text{ }^{\circ}\text{C}$		1200	V
I_C	$T_j = 150\text{ }^{\circ}\text{C}$	$T_{case} = 25\text{ }^{\circ}\text{C}$	300	A
		$T_{case} = 80\text{ }^{\circ}\text{C}$	210	A
I_{CRM}	$I_{CRM}=2I_{Cnom}$		400	A
V_{GES}			± 20	V
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ }^{\circ}\text{C}$ $V_{CES} < 1200\text{ V}$		10	μs
Inverse Diode				
I_F	$T_j = 150\text{ }^{\circ}\text{C}$	$T_{case} = 25\text{ }^{\circ}\text{C}$	260	A
		$T_{case} = 80\text{ }^{\circ}\text{C}$	180	A
I_{FRM}	$I_{FRM}=2I_{Fnom}$		400	A
I_{FSM}	$t_p = 10\text{ ms}; \sin.$ $T_j = 150\text{ }^{\circ}\text{C}$		1800	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			- 40...+ 150	$^{\circ}\text{C}$
T_{stg}			- 40...+ 125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.		4000	V

Characteristics			T _c = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 8 mA		4,5	5,5	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _J = 25 °C			0,1	0,3	mA
V _{CE0}	T _J = 25 °C			1,5	1,75	V
	T _J = 125 °C			1,7		V
r _{CE}	V _{GE} = 15 V T _J = 25°C			9	10,5	mΩ
	T _J = 125°C			11,5		mΩ
V _{CE(sat)}	I _{Cnom} = 200 A, V _{GE} = 15 V T _J = °C _{chiplev.}			3,3	3,85	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz			18	24	nF
C _{oes}				2,5	3,2	nF
C _{res}				1	1,3	nF
Q _G	V _{GE} = 0V - +20V			2000		nC
R _{Gint}	T _J = °C			2,5		Ω
t _{d(on)}	R _{Gon} = 3 Ω	V _{CC} = 600V I _C = 200A			130	ns
t _r					40	ns
E _{on}	R _{Goff} = 3 Ω	T _J = 125 °C V _{GE} = ± 15V			16	mJ
t _{d(off)}					460	ns
t _f					30	ns
E _{off}						mJ
R _{th(j-c)}	per IGBT		0,075			K/W

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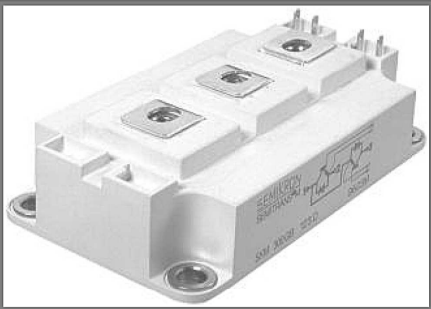
Characteristics

Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 200$ A; $V_{GE} = 0$ V				
	$T_j = 25$ °C _{chiplev.}		2	2,5	V
	$T_j = 125$ °C _{chiplev.}		1,8		V
V_{F0}					
	$T_j = 25$ °C		1,1	1,2	V
	$T_j = 125$ °C				V
r_F					
	$T_j = 25$ °C		4,5	6,5	mΩ
	$T_j = 125$ °C				mΩ
I_{RRM}	$I_F = 200$ A		340		A
Q_{rr}	$di/dt = 8000$ A/μs		46		μC
E_{rr}	$V_{GE} = 0$ V; $V_{CC} = 600$ V				mJ
$R_{th(j-c)D}$	per diode			0,18	K/W
Module					
L_{CE}			15	20	nH
$R_{CC'+EE'}$	res., terminal-chip				
	$T_{case} = 25$ °C		0,35		mΩ
	$T_{case} = 125$ °C		0,5		mΩ
$R_{th(c-s)}$	per module			0,038	K/W
M_s	to heat sink M6		3	5	Nm
M_t	to terminals M6		2,5	5	Nm
w				325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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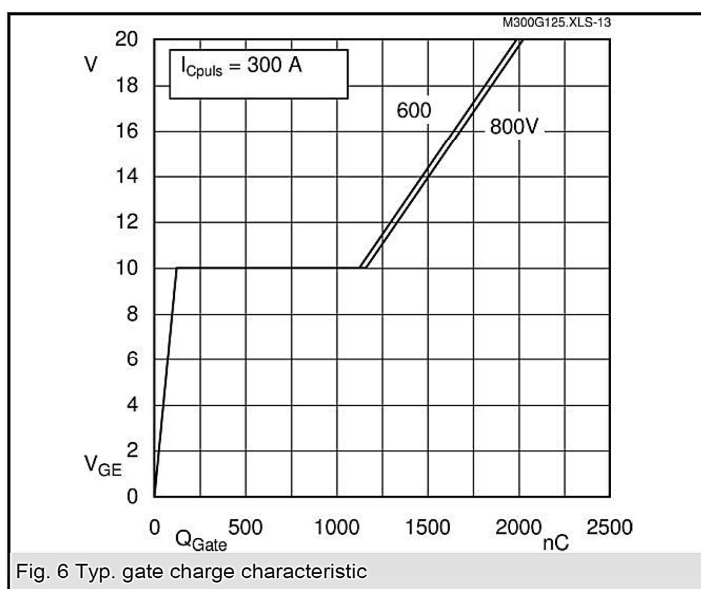
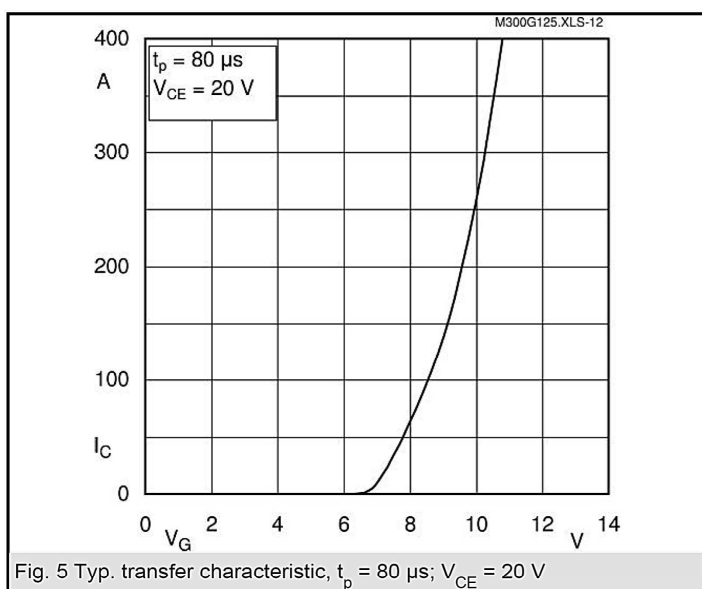
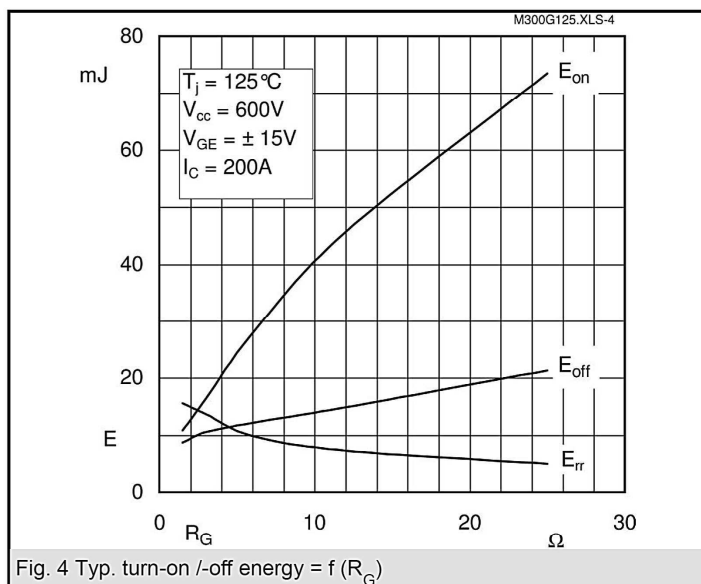
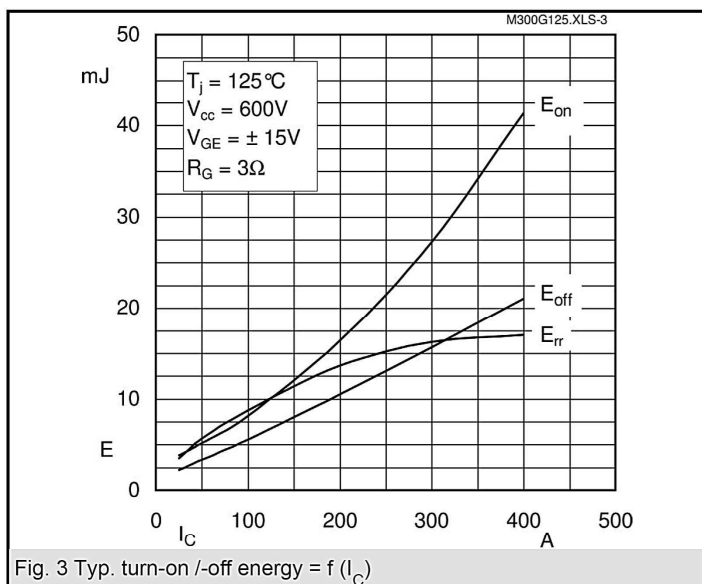
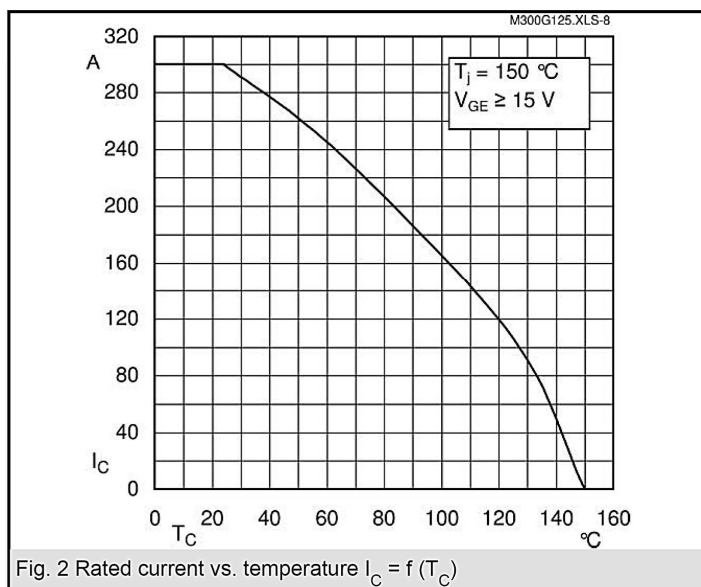
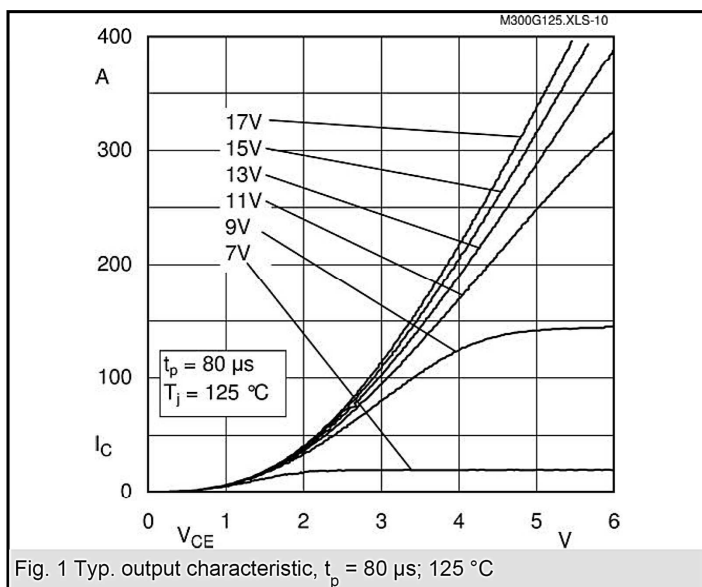
Typical Applications*

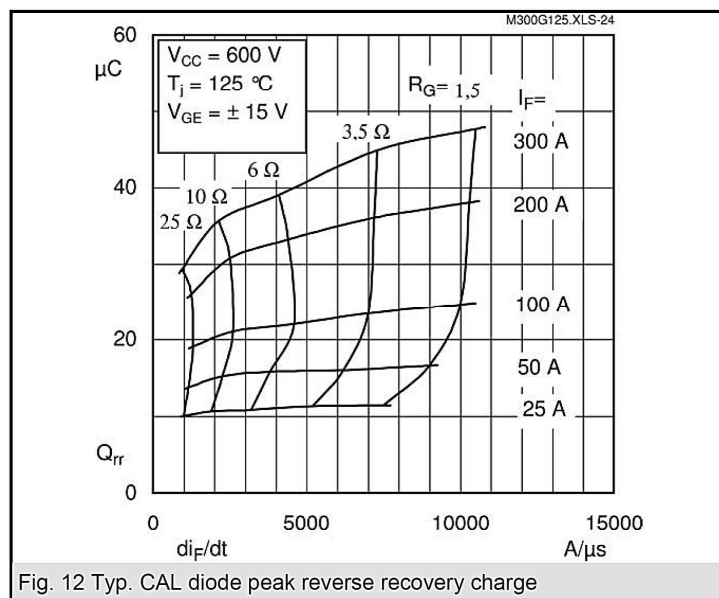
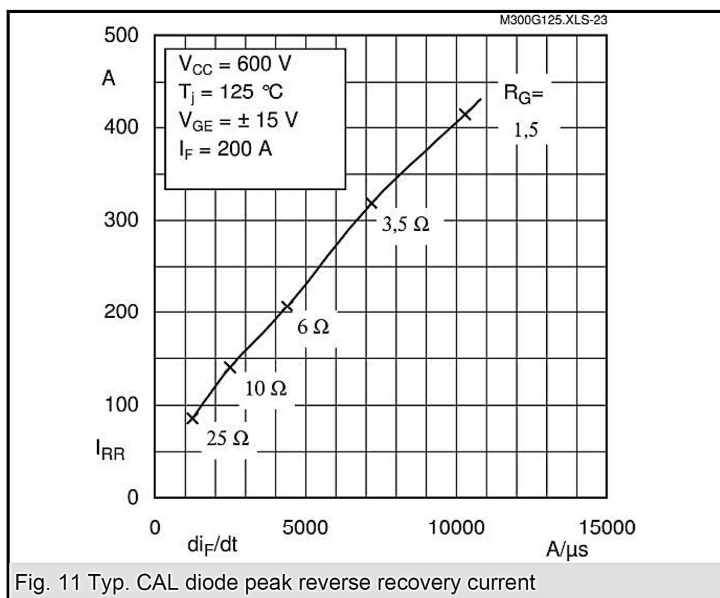
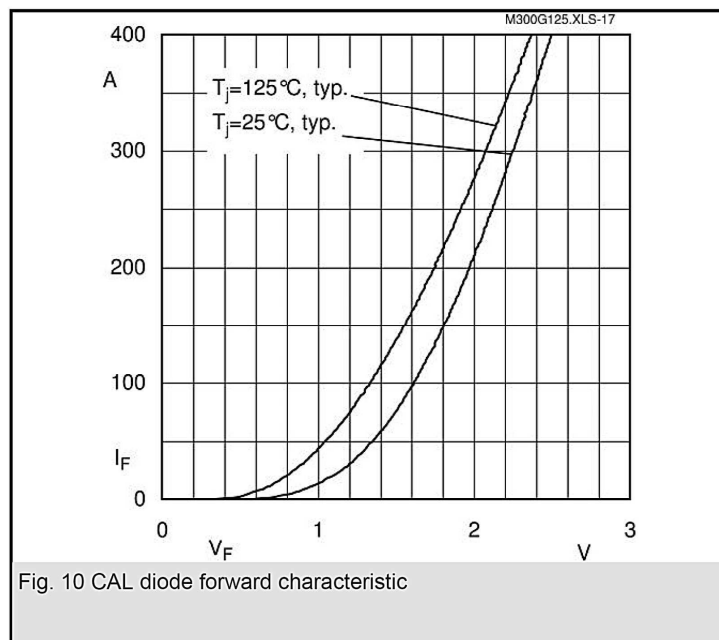
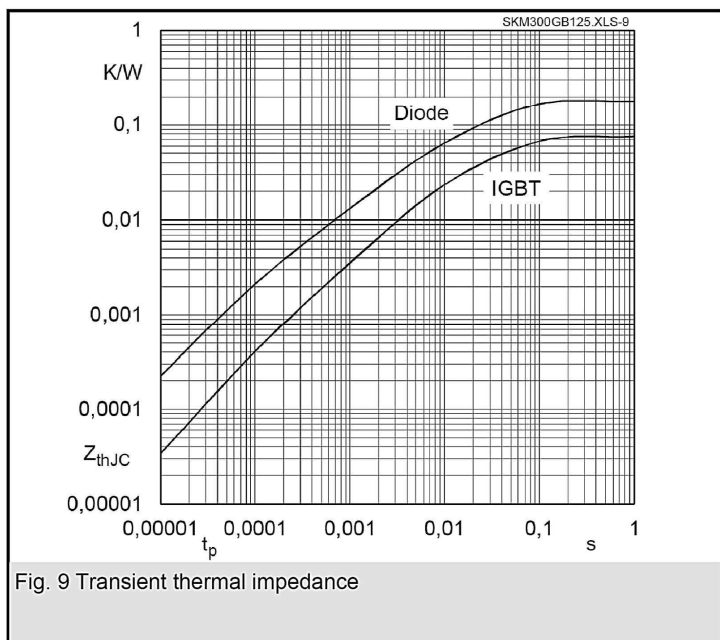
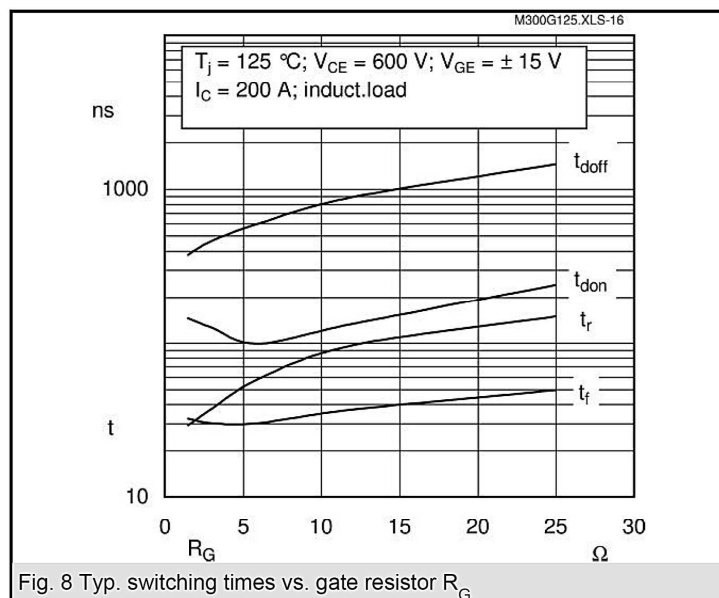
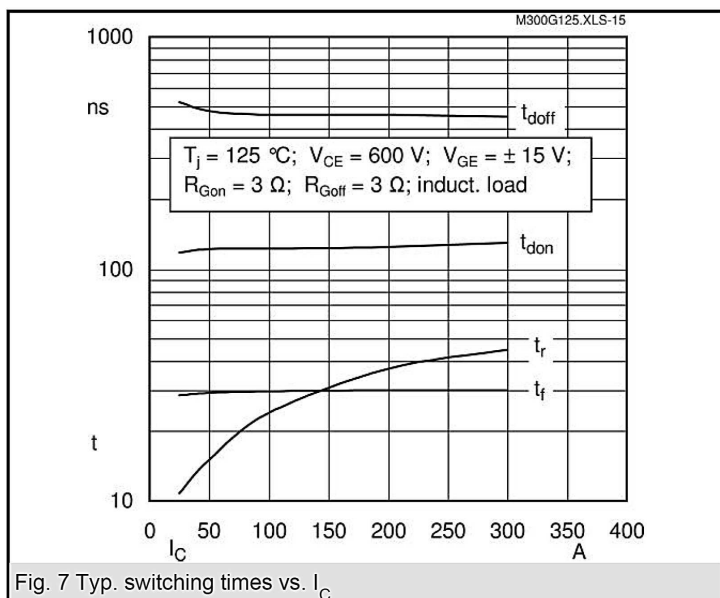
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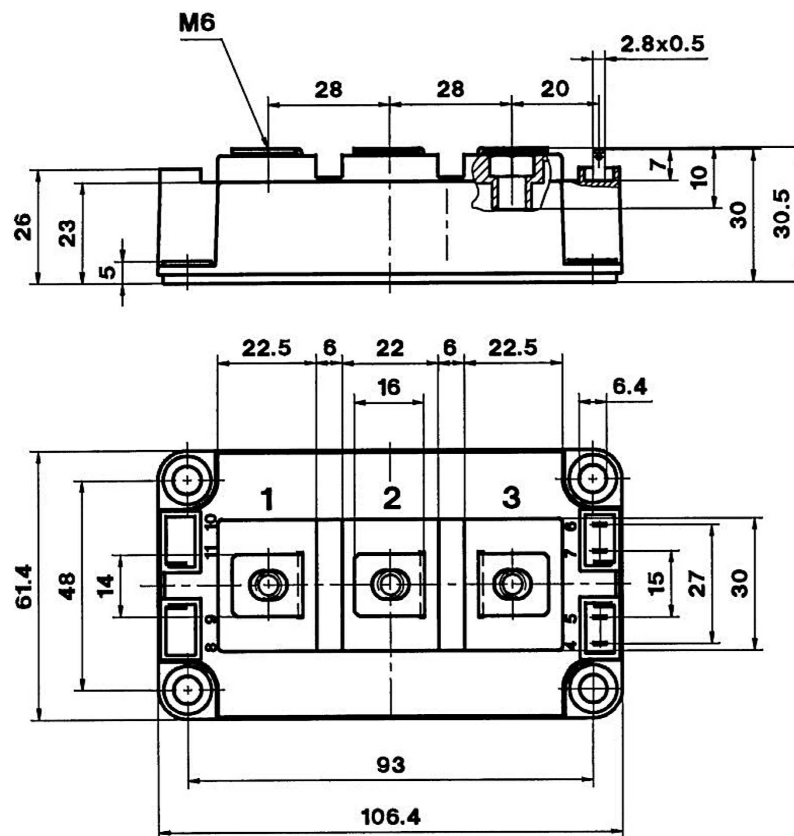


GB

Z_{th}			
Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	$i = 1$	53	mK/W
R_i	$i = 2$	18,5	mK/W
R_i	$i = 3$	3,1	mK/W
R_i	$i = 4$	0,4	mK/W
τ_{ui}	$i = 1$	0,04	s
τ_{ui}	$i = 2$	0,0189	s
τ_{ui}	$i = 3$	0,0017	s
τ_{ui}	$i = 4$	0,003	s
$Z_{th(j-c)D}$			
R_i	$i = 1$	115	mK/W
R_i	$i = 2$	52	mK/W
R_i	$i = 3$	11	mK/W
R_i	$i = 4$	2	mK/W
τ_{ui}	$i = 1$	0,0366	s
τ_{ui}	$i = 2$	0,0113	s
τ_{ui}	$i = 3$	0,003	s
τ_{ui}	$i = 4$	0,0002	s







Case D 56

